

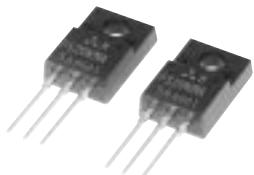
**PRELIMINARY**  
Notice: This is not a final specification.  
Some parametric limits are subject to change.

MITSUBISHI Nch POWER MOSFET

# FS20KMA-5A

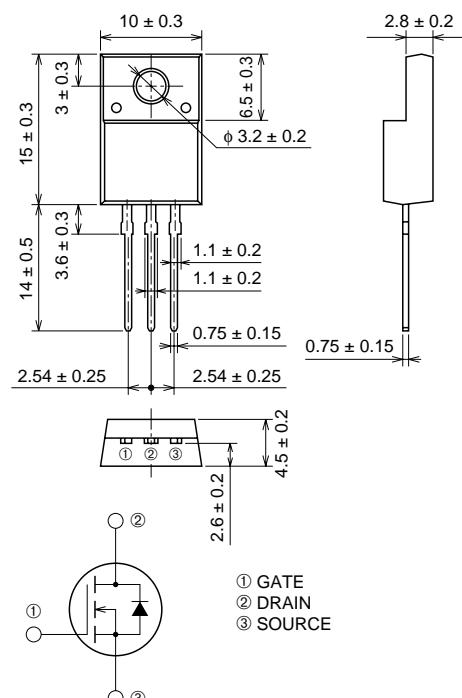
HIGH-SPEED SWITCHING USE

## FS20KMA-5A



- 10V DRIVE
- V<sub>DSS</sub> ..... 250V
- r<sub>Ds</sub> (ON) (MAX) ..... 0.20Ω
- I<sub>D</sub> ..... 20A

## OUTLINE DRAWING



## APPLICATION

Cs Switch for CRT Display monitor

## MAXIMUM RATINGS ( $T_c = 25^\circ\text{C}$ )

Symbol	Parameter	Conditions	Ratings	Unit
V <sub>DSS</sub>	Drain-source voltage	V <sub>GS</sub> = 0V	250	V
V <sub>GSS</sub>	Gate-source voltage	V <sub>DS</sub> = 0V	±20	V
I <sub>D</sub>	Drain current		20	A
I <sub>DM</sub>	Drain current (Pulsed)		60	A
I <sub>DA</sub>	Avalanche drain current (Pulsed)	L = 200μH	20	A
P <sub>D</sub>	Maximum power dissipation		40	W
T <sub>ch</sub>	Channel temperature		-55 ~ +150	°C
T <sub>stg</sub>	Storage temperature		-55 ~ +150	°C
V <sub>iso</sub>	Isolation voltage	AC for 1 minute, Terminal to case	2000	V
—	Weight	Typical value	2.0	g

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**ELECTRICAL CHARACTERISTICS** ( $T_{ch} = 25^\circ\text{C}$ )

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$Id = 1\text{mA}$ , $V_{GS} = 0\text{V}$	250	—	—	V
$I_{GSS}$	Gate-source leakage current	$V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$	—	—	$\pm 10$	$\mu\text{A}$
$I_{DSS}$	Drain-source leakage current	$V_{DS} = 250\text{V}$ , $V_{GS} = 0\text{V}$	—	—	1	mA
$V_{GS(\text{th})}$	Gate-source threshold voltage	$Id = 1\text{mA}$ , $V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
$r_{DS(\text{ON})}$	Drain-source on-state resistance	$Id = 10\text{A}$ , $V_{GS} = 10\text{V}$	—	0.15	0.20	$\Omega$
$V_{DS(\text{ON})}$	Drain-source on-state voltage	$Id = 10\text{A}$ , $V_{GS} = 10\text{V}$	—	1.50	2.00	V
$ y_{fs} $	Forward transfer admittance	$Id = 10\text{A}$ , $V_{DS} = 10\text{V}$	—	20.0	—	S
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{V}$ , $V_{GS} = 0\text{V}$ , $f = 1\text{MHz}$	—	2250	—	pF
$C_{oss}$	Output capacitance		—	220	—	pF
$C_{rss}$	Reverse transfer capacitance		—	65	—	pF
$t_{d(\text{on})}$	Turn-on delay time	$V_{DD} = 150\text{V}$ , $Id = 10\text{A}$ , $V_{GS} = 10\text{V}$ , $R_{GEN} = R_{GS} = 50\Omega$	—	35	—	ns
$t_r$	Rise time		—	60	—	ns
$t_{d(\text{off})}$	Turn-off delay time		—	400	—	ns
$t_f$	Fall time		—	90	—	ns
$V_{SD}$	Source-drain voltage	$Is = 10\text{A}$ , $V_{GS} = 0\text{V}$	—	0.95	—	V
$R_{th(\text{ch-c})}$	Thermal resistance	Channel to case	—	—	3.13	$^\circ\text{C}/\text{W}$